

CD74HC365, CD74HCT365, CD74HC366, CD74HCT366

High Speed CMOS Logic Hex Buffer/Line Driver, Three-State Non-Inverting and Inverting

Features

- Buffered Inputs
- High Current Bus Driver Outputs
- Typical Propagation Delay $t_{PLH}, t_{PHL} = 8\text{ns}$ at $V_{CC} = 5\text{V}$, $C_L = 15\text{pF}$, $T_A = 25^\circ\text{C}$
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5\text{V}$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8\text{V}$ (Max), $V_{IH} = 2\text{V}$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu\text{A}$ at V_{OL}, V_{OH}

Description

The Harris CD74HC365, CD74HCT365, CD74HC366, and CD74HCT366 silicon gate CMOS three-state buffers are general purpose high-speed non-inverting and inverting buffers. They have high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuitry, yet have speeds comparable to low power Schottky TTL circuits. Both circuits are capable of driving up to 15 low power Schottky inputs.

The CD74HC365 and CD74HCT365 are non-inverting buffers, whereas the CD74HC366 and CD74HCT366 are inverting buffers. These devices have two three-state control inputs ($\overline{\text{OE}}1$ and $\overline{\text{OE}}2$) which are NORed together to control all six gates.

The CD74HCT365 and CD74HCT366 logic families are speed, function and pin compatible with the standard 74LS logic family.

Ordering Information

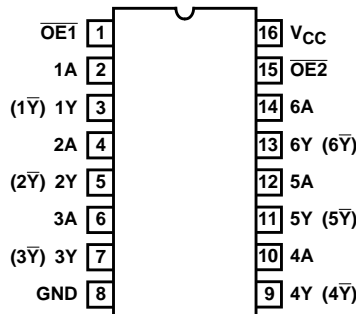
PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC365E	-55 to 125	16 Ld PDIP	E16.3
CD74HCT365E	-55 to 125	16 Ld PDIP	E16.3
CD74HC366E	-55 to 125	16 Ld PDIP	E16.3
CD74HC365M	-55 to 125	16 Ld SOIC	M16.15
CD74HCT365M	-55 to 125	16 Ld SOIC	M16.15

NOTES:

1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

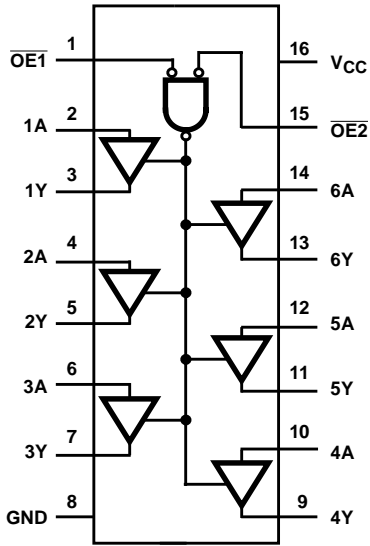
Pinout

CD74HC365, CD74HCT365, CD74HC366, CD74HCT366
(PDIP, SOIC)
TOP VIEW

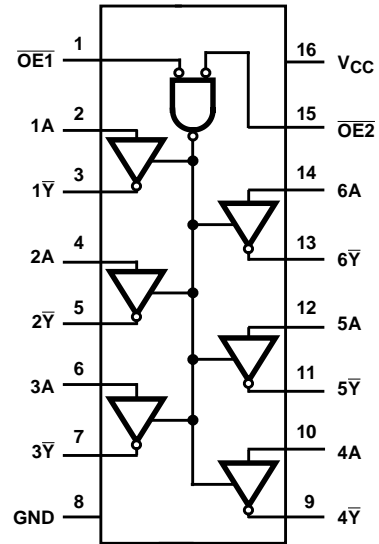


Functional Diagrams

CD74HC365, CD75HCT365



CD74HC366, CD75HCT366

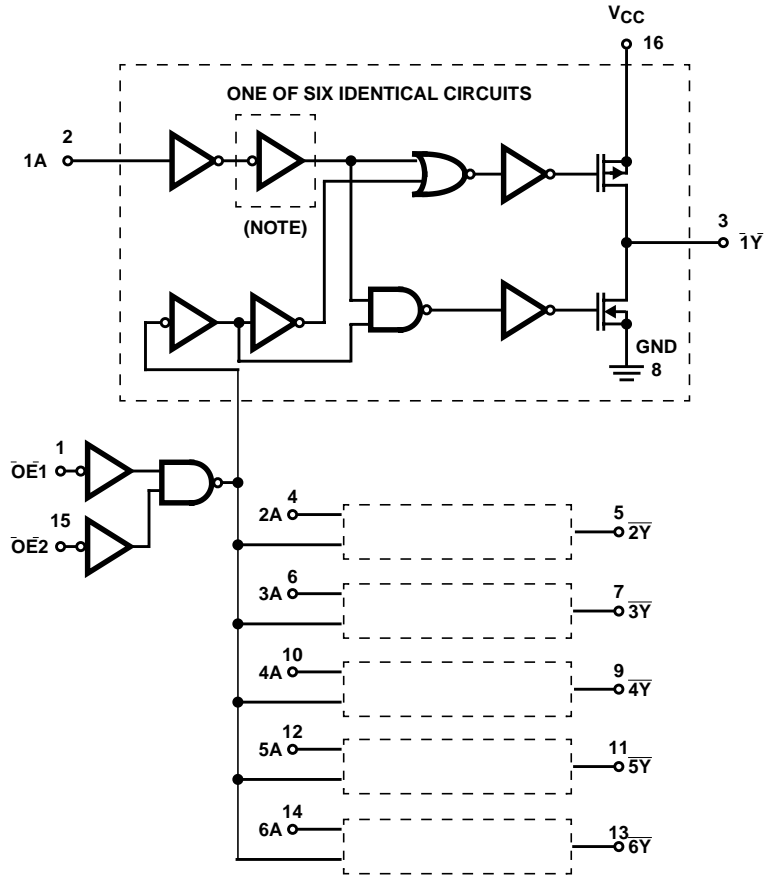


TRUTH TABLE

INPUTS			OUTPUTS (Y)	
OE1	OE2	A	HC/HCT365	HC/HCT366
L	L	L	L	H
L	L	H	H	L
X	H	X	Z	Z
H	X	X	Z	Z

NOTE:
 H = High Voltage Level
 L = Low Voltage Level
 X = Don't Care
 Z = High Impedance (OFF) State

Logic Diagram



NOTE: Inverter not included in HC/HCT365.

FIGURE 1. LOGIC DIAGRAM FOR THE HC/HCT365 AND HC/HCT366 (OUTPUTS FOR HC/HCT365 ARE COMPLEMENTS OF THOSE SHOWN, i.e., 1Y, 2Y, ETC.)

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Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	$\pm 20mA$
DC Drain Current, per Output, I_O	
For $-0.5V < V_O < V_{CC} + 0.5V$	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	$\pm 25mA$
DC V_{CC} or Ground Current, I_{CC}	$\pm 50mA$

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} (°C/W)
PDIP Package	90
SOIC	115
Maximum Junction Temperature	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C (SOIC - Lead Tips Only)

Operating Conditions

Temperature Range, T_A	-55°C to 125°C
Supply Voltage Range, V_{CC}	
HC Types2V to 6V
HCT Types	4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS	
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX		
HC TYPES													
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V	
				4.5	3.15	-	-	3.15	-	3.15	-	V	
				6	4.2	-	-	4.2	-	4.2	-	V	
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V	
				4.5	-	-	1.35	-	1.35	-	1.35	V	
				6	-	-	1.8	-	1.8	-	1.8	V	
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	-0.02	6	5.9	-	-	5.9	-	5.9	-	V
			-6	-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	V_{OL}	V_{IH} or V_{IL}	6	6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	± 0.1	-	± 1	-	± 1	μA	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	μA	

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DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	V _O = V _{CC} or GND	6	-	-	±0.5	-	±5.0	-	±10	μA
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI _{CC}	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	V _O = V _{CC} or GND	5.5	-	-	±0.5	-	±5.0	-	±10	μA

NOTE:

4. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
$\overline{OE}1$	0.6
All Others	0.55

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360μA max at 25°C.

Switching Specifications - HC/HCT365 Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V _{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay, Data to Outputs HC/HCT365	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	105	130	160	ns
			4.5	-	21	26	32	ns
			6	-	18	22	27	ns
		C _L = 15pF	5	8	-	-	-	ns

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Switching Specifications - HC/HCT365 Input $t_r, t_f = 6\text{ns}$ (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
Propagation Delay, Data to Outputs HC/HCT366	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	2	-	110	140	165	ns
			4.5	-	22	28	33	ns
			6	-	19	24	28	ns
		$C_L = 15\text{pF}$	5	9	-	-	-	ns
Propagation Delay, Output Enable and Disable to Outputs	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	2	-	150	190	225	ns
			4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		$C_L = 15\text{pF}$	5	12	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	40	-	-	-	pF

HCT TYPES

Propagation Delay, Data to Outputs HC/HCT365	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	25	31	38	ns
		$C_L = 15\text{pF}$	5	9	-	-	-	ns
Propagation Delay, Data to Outputs HC/HCT366	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	27	34	41	ns
		$C_L = 15\text{pF}$	5	11	-	-	-	ns
Propagation Delay, Output Enable and Disable to Outputs	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	35	44	53	ns
		$C_L = 15\text{pF}$	5	14	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	4.5	-	12	15	18	ns
Input Capacitance	C_{IN}	-	-	-	10	10	10	pF
Three-State Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C_{PD}	-	5	42	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per buffer.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

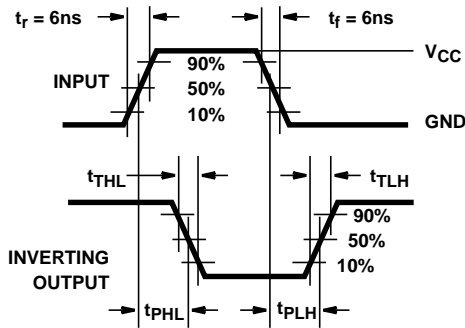


FIGURE 2. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

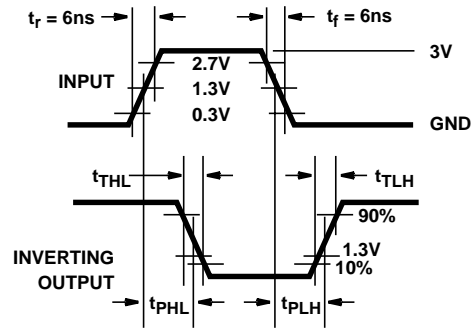


FIGURE 3. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

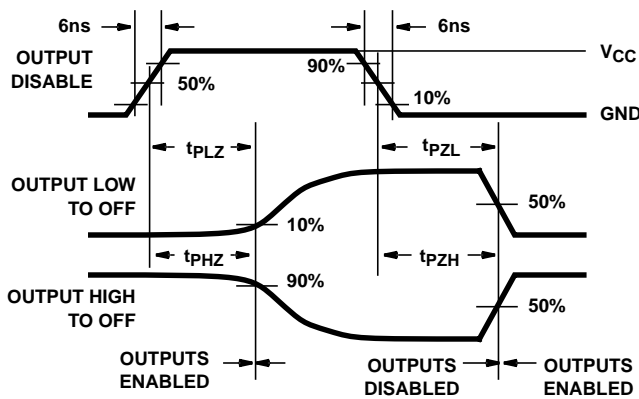


FIGURE 4. HC THREE-STATE PROPAGATION DELAY WAVEFORM

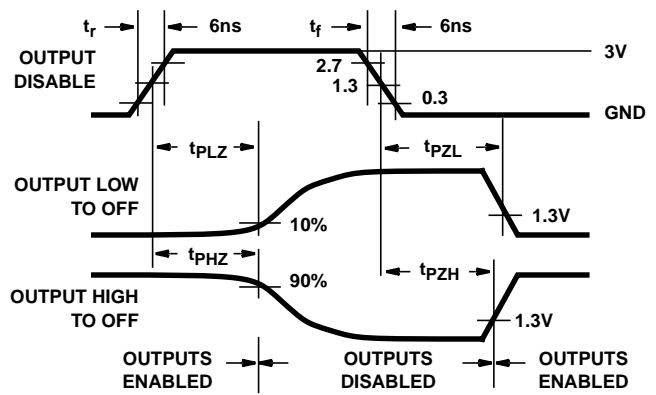
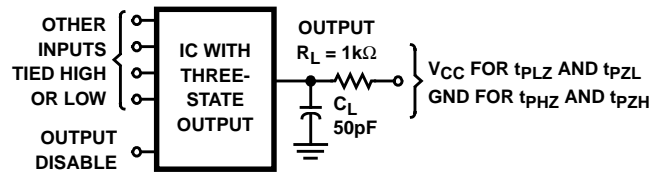


FIGURE 5. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{pLZ} and t_{pZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ V_{CC} , $C_L = 50pF$.

FIGURE 6. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

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